

廖洺漢

著作目錄

期刊論文

1. S. Sakalley, A. Saravanan, W.-C. Cheng, S.-C. Chen, H. Sun, B.-R. Huang, and M.-H. Liao, (2023, Jan). High performance self-powered UV photo detection by ZnO/Cu₃N core-shell nano-rod hetero-structures via p-n junction formation. *Journal of Alloys and Compounds*, Vol. 69(9), p. 5386-5390..
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